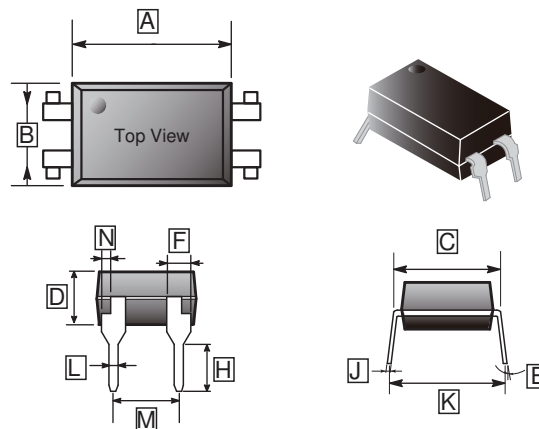


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The BL814 series of devices each consist of an infrared Emitting diodes, optically coupled to a phototransistor detector. They are packaged in a 4-pin DIP package and available in Wide-lead spacing and SMD option.

DIP4



FEATURES

- Current transfer ratio (CTR: 20%-300% at $I_F=1\text{mA}, V_{CE}=5\text{V}$)
- High isolation voltage between input and output ($V_{iso} = 5000\text{V rms}$)
- Creepage distance > 7.62mm
- UL/CUL Approved (File No. E340048)

APPLICATIONS

- Programmable controllers
- System appliances, measuring instruments
- Telecommunication equipments
- Home appliances, such as fan heaters, etc.
- Signal transmission between circuits of different potentials and impedances

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min..	Max
A	6.30	6.70	H	2.60	3.00
B	4.40	4.80	J	0.20	0.30
C	7.9	8.3	K	8.65	9.35
D	3.20	3.75	L	0.50 TYP.	
E	2°	8°	M	2.40	2.70
F	1.25 TYP.		N	0.40 TYP.	

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Rating	Unit
Input	Forward Current	I_F	± 50	mA
	Peak forward current($t=10\mu\text{s}$)	I_{FM}	1	A
	Power dissipation Derating factor(above 100°C)	P_D	70 2.9	mW mW / $^\circ\text{C}$
Output	Collector-Emitter Voltage	V_{CEO}	80	V
	Emitter-Collector Voltage	V_{ECO}	6	
	Power dissipation Derating factor(above 100°C)	P_C	150 5.8	mW mW / $^\circ\text{C}$
Total Power Dissipation		P_{tot}	200	mW
Isolation Voltage ¹		V_{iso}	5000	V rms
Operating Temperature		T_{opr}	-55~110	$^\circ\text{C}$
Storage Temperature		T_{stg}	-55~125	
Soldering Temperature ²		T_{sol}	260	

Note :

1. AC for 1 minute, R.H.=40~60% R.H. In this test, pins 1&2 are shorted together , and pins 3&4 are shorted together.
2. For 10 Seconds.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions	
Input	Forward Voltage	V_F	-	1.2	1.4	V	$I_F = \pm 20\text{mA}$	
	Input capacitance	C_{in}	-	50	250	pF	$V = 0, f = 1\text{KHz}$	
Output	Collector Dark Current	I_{CEO}	-	-	100	nA	$V_{CE} = 20\text{V}, I_F = 0$	
	Collector-Emitter Breakdown Voltage	BV_{CEO}	80	-	-	V	$I_C = 0.1\text{mA}$	
	Emitter-Collector Breakdown Voltage	BV_{ECO}	6	-	-	V	$I_E = 0.1\text{mA}$	
Transfer Characteristics	Current Transfer Ratio	BL814	CTR	20	-	300	%	$V_{CE} = 5\text{V}, I_F = \pm 1\text{mA}$
		BL814A		50	-	150		
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	0.05	0.2	V	$I_F = \pm 20\text{mA}, I_C = 1\text{mA}$	
	Isolation Resistance	R_{IO}	5×10^{10}	10^{11}	-	Ω	$V_{IO} = 500\text{Vdc}, 40 \sim 60\% \text{R.H.}$	
	Floating Capacitance	C_{IO}	-	0.6	1	pF	$V_{IO} = 0, f = 1\text{MHz}$	
	Cut-Off Frequency	f_C	-	80	-	KHz	$V_{CE} = 5\text{V}, I_C = 2\text{mA}, R_L = 100\Omega, -3\text{dB}$	
	Response Time(Rise)	t_r	-	7	18	μs	$V_{CE} = 2\text{V}, I_C = 2\text{mA}, R_L = 100\Omega$	
	Response Time(Fall)	t_f	-	11	18	μs		

CHARACTERISTIC CURVE

Fig.1 Forward Current vs. Ambient Temperature

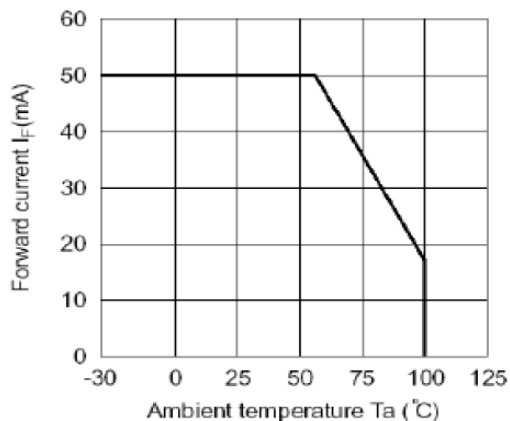


Fig.2 Collector Power Dissipation vs. Ambient Temperature

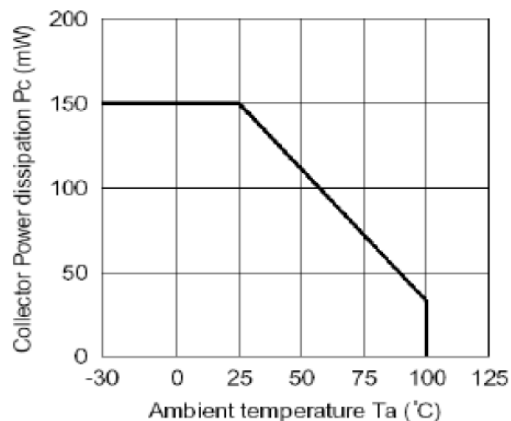


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

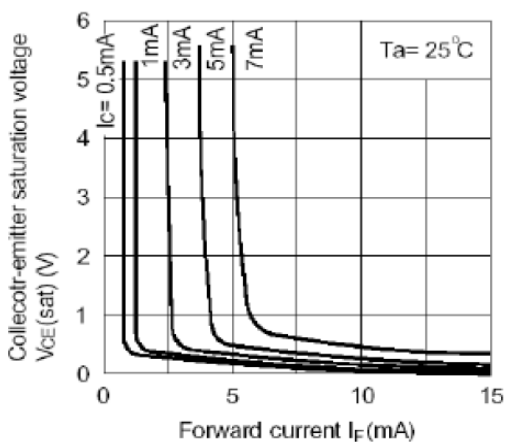


Fig.4 Forward Current vs. Forward Voltage

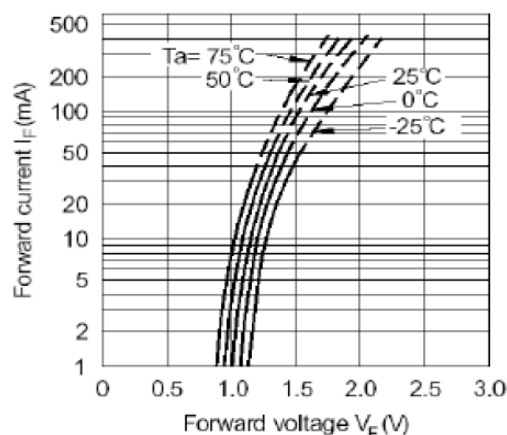


Fig.5 Current Transfer Ratio vs. Forward Current

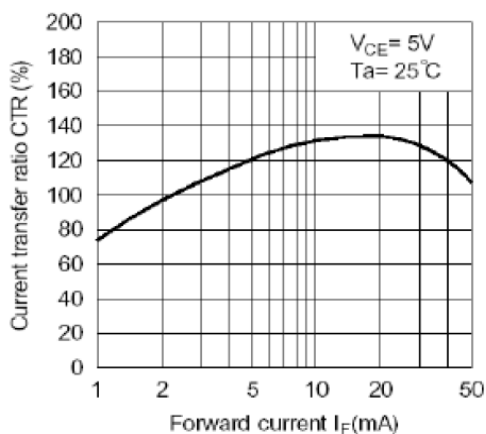
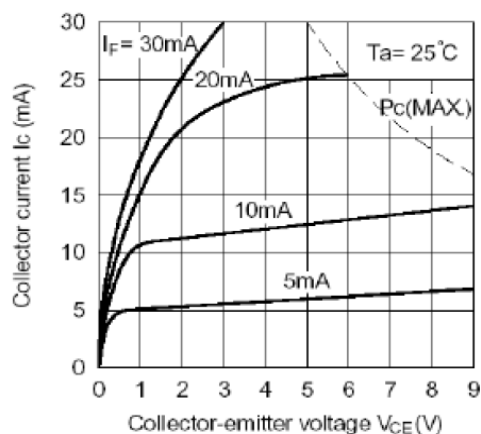


Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTIC CURVE

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

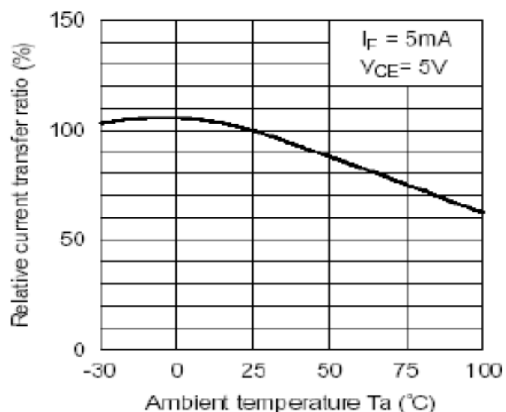


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

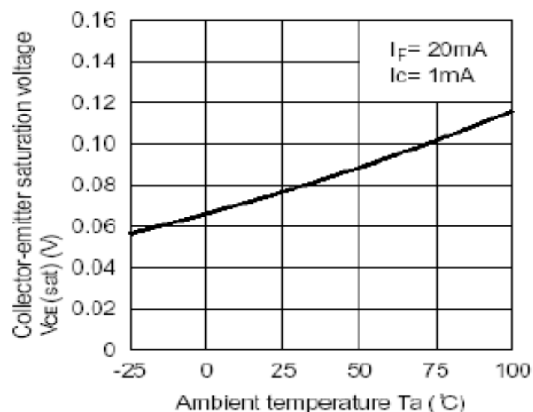


Fig.9 Collector Dark Current vs. Ambient Temperature

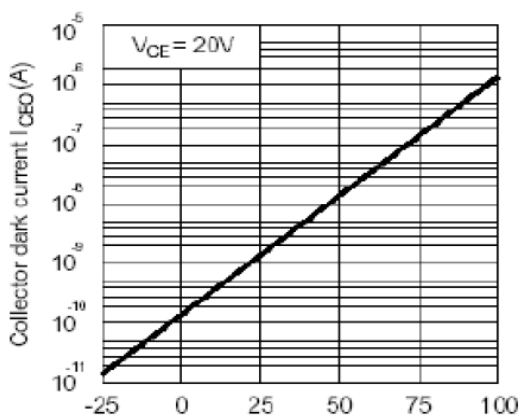


Fig.10 Response Time vs. Load Resistance

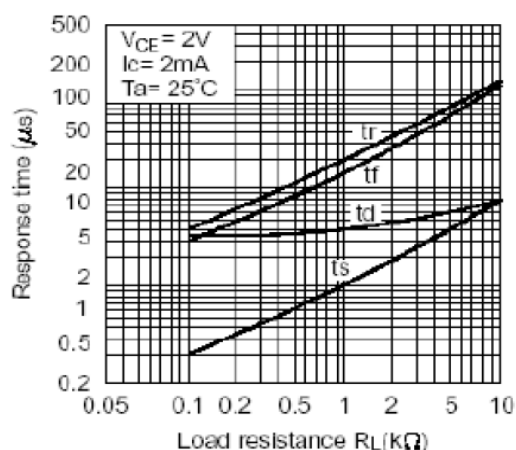
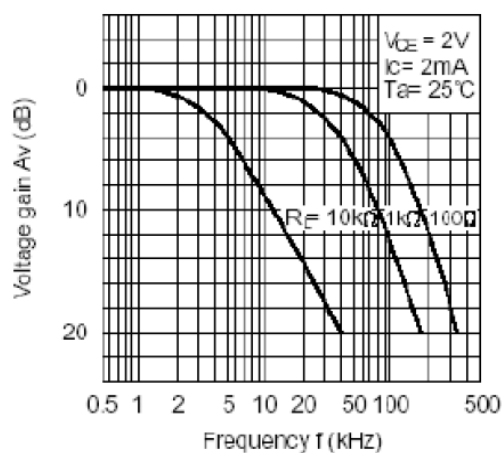
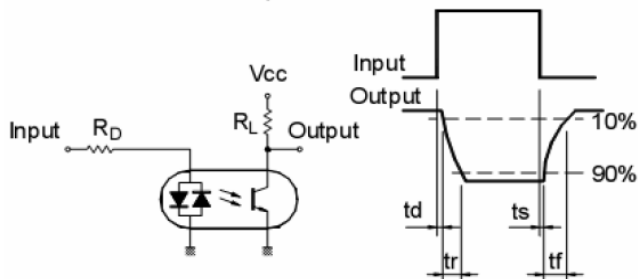


Fig.11 Frequency Response



Test Circuit for Response Time



Test Circuit for Frequency Response

